

# Citations for Ion : **Pt**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1976	Grant, W. A. Dodds, D. Williams, J. S. Christodoulides, C. E. Baragiola, R. A. <b>'Heavy Ion Ranges in Silicon and Aluminum'</b> <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 693-703 (1976)</i>	1976-Gran
	<i>Comment : R. 0.01 &lt; Epsilon &lt; 0.8 Cr, Ni, Ga, As, Br, Mo, Cs, La, Nd, Dy, Ta, Pt, Au, Pb -&gt; Si, Al</i>	
1978	Combasson, J. L. Farmery, B. W. McCulloch, D. Neilson, G. W. Thompson, M. W. <b>'Heavy Ion Ranges in Aluminum and Silicon'</b> <i>Rad. Effects, 36, 149-156 (1978)</i>	1978-Comb
	<i>Comment : R, dR. 20-250 keV Cs, La, Pr, Eu, Tb, Dy, Ho, Er, Lu, Hf, Pt, Au, Tl, Pb, Bi -&gt; Al; Sm, Eu, Gd, Tb, Dy -&gt; Si</i>	
1980	Besenbacher, F. Bottiger, J. Laursen, T. Loftager, P. Moller, W. <b>'Z1-Oscillations in Low-Energy Heavy-Ion Ranges'</b> <i>Nucl. Inst. Methods, 170, 183-188 (1980)</i>	1980-Bese2
	<i>Comment : R, dR. Atomic Numbers 18-92 (epsilon=.015) -&gt; Si</i>	
1982	Geissel, H. Laichter, Yl Schneider, W. F. W. Armbruster, P. <b>'Energy Loss and Energy Loss Straggling of Fast Heavy Ions in Matter'</b> <i>Nucl. Inst. Methods, 194, 21-29 (1982)</i>	1982-Geis
	<i>Comment : S. Heavy Ions (18 - 92) at 0.5-10 MeV/amu -&gt; 17 Solids and 5 Gases</i>	
1988	Wilson, R. G. <b>'(111) Random and (110) Channeling Implantation Profiles and Range Parameters in HgCdTe'</b> <i>J. Appl. Phys., 63, 5302-5311 (1988)</i>	1988-Wils
	<i>Comment : R, dR. 45 Ions (H to Ta) at 100-700 keV -&gt; HgCdTe</i>	
1988	Wilson, R. G. <b>'Ion Implantation and SIMS Profiling of Impurities in II-VI Materials HgCdTe and CdTe'</b> <i>J. Crystal Growth, 86, 735-743 (1988)</i>	1988-Wils2
	<i>Comment : R, dR. 52 Ions (H-Hg) at 100-700 keV -&gt; CdTe, HgCdTe</i>	